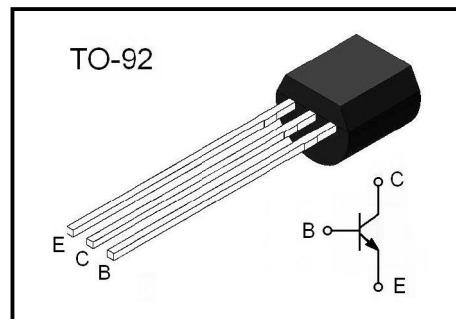


NPN Plastic-Encapsulate Transistors
High Voltage Mode Application

High speed Switching

Marking Code	
YFW13003B	YFW 13003B


Absolute Maximum Rating (Ta=25°C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV _{CBO}	700	V
Collector-Emitter Voltage	BV _{CEO}	400	V
Emitter-Base Voltage	B _{VEBO}	9	V
Collector Current	I _C	0.5	A
Collector Power Dissipation	P _C	0.9	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~150	°C

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BV _{CBO}	I _C = 100μA, I _E = 0	700			V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA, I _B = 0	400			V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 100μA, I _C = 0	9			V
Collector cut-off current	I _{CBO}	V _{CB} = 700V, I _E = 0			100	μA
Collector cut-off current	I _{CEO}	V _{CE} = 400V, I _B = 0			200	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 9V, I _C = 0			100	μA
DC current gain*	h _{FE}	V _{CE} = 5, I _C = 0.1A	10		40	
Collector-emitter saturation voltage*	V _{CE(sat)}	I _C = 0.5A, I _B = 0.1A			0.5	V
Base -emitter saturation voltage*	V _{BE(sat)}	I _C = 0.5A, I _B = 0.1A			1.2	V
Transition frequency	f _T	V _{CE} = 10V, I _B = 0.1A	8			MHz
Output Capacitance	C _{ob}	V _{CE} = 10V, f = 1MHz		21		pF
Turn On Time	t _{on}	V _{CC} = 10V, I _C = 0.1A			1.1	μs
Storage Time	t _{stg}	I _{B1} = 0.2A, I _{B2} = -0.1A			4.0	μs
Fall Time	t _f	RL = 125Ω			0.7	μs

* Pulse Test: Pulse Width=5ms, Duty Cycle≤10%

Typical Characteristics

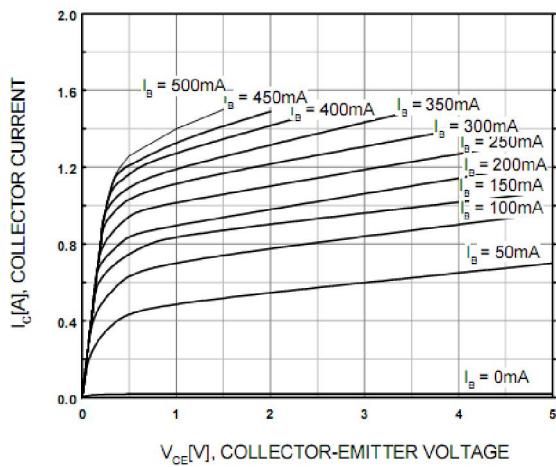


Figure 1. Static Characteristic

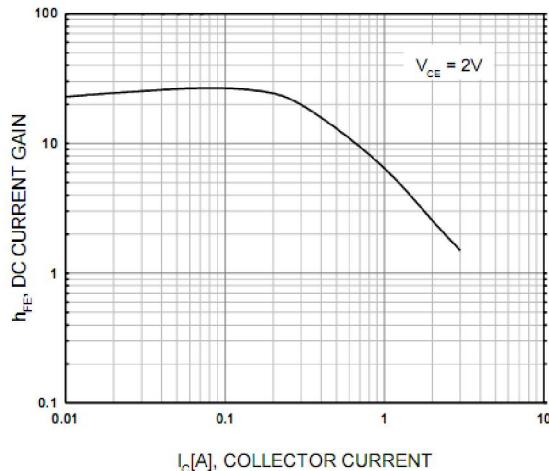
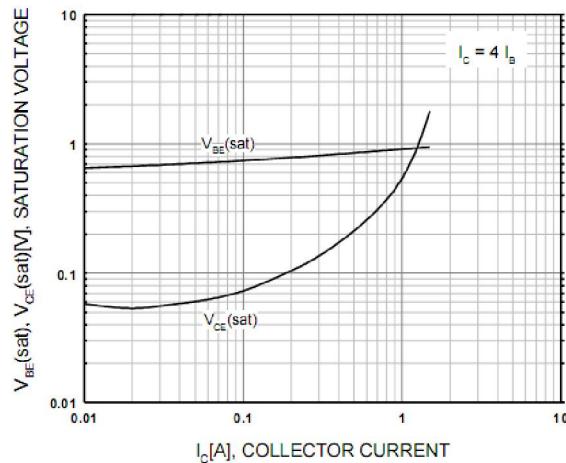


Figure 2. DC current Gain



**Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage**

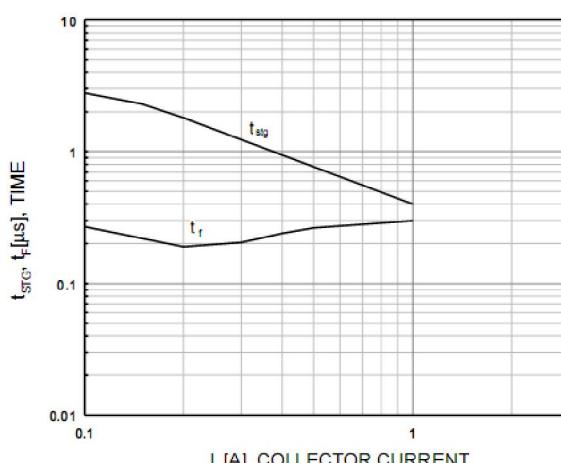


Figure 4. Switching Time

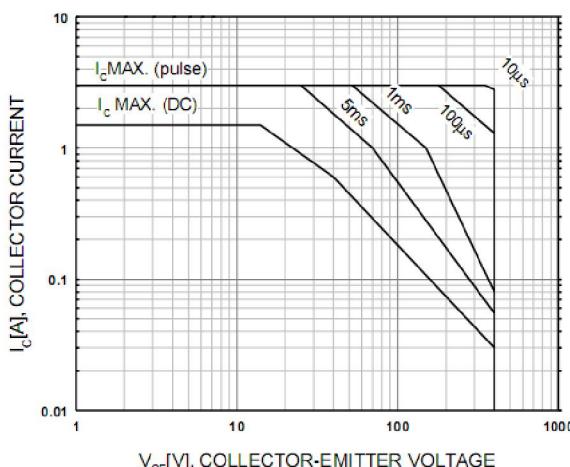


Figure 5. Safe Operating Area

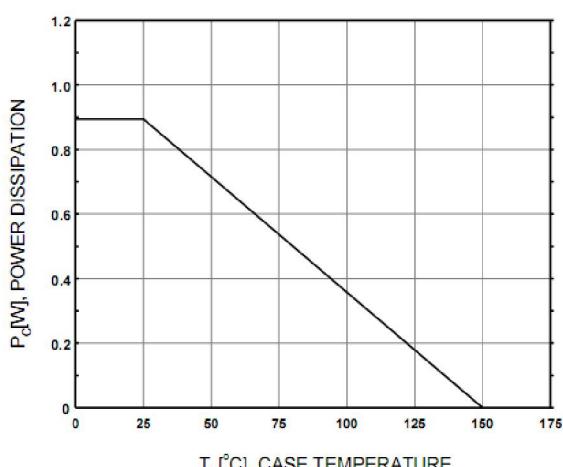


Figure 6. Power Derating

Ordering information

Package	Packing Description	Base Quantity
TO-92	Bulk	1000pcs/Bag
	Tape	2000pcs/Box

Package Dimensions

TO-92

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.70	0.130	0.146
A1	2.30	2.70	0.091	0.106
b	0.40	0.50	0.016	0.020
b1	0.50	0.70	0.020	0.028
c	0.35	0.45	0.014	0.018
D	4.45	4.70	0.175	0.185
E	4.40	4.65	0.173	0.183
e	1.17	1.37	0.046	0.054
e1	2.34	2.64	0.092	0.104
L	13.50	14.50	0.531	0.571
L1	1.80	2.20	0.071	0.087

Disclaimer

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices). YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.